Quad Complementary Pair Transistor

Symbol

VCEO

VCBO

VEBO

IC

 P_{D}

 P_D

TJ, Tstg

Value

40

40

5.0

200

-55 to +150

Each

Transistor

500

4.0

825

6.7

Four

Transistors

Equal Power

900

7.2

2400

19.2

NPN/PNP Silicon

MAXIMUM RATINGS

Collector-Emitter Voltage

Collector-Base Voltage

Emitter-Base Voltage

Total Device Dissipation

Derate above 25°C

Total Device Dissipation

Derate above 25°C

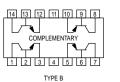
Temperature Range

@ $T_A = 25^{\circ}C^{(1)}$

@ $T_{C} = 25^{\circ}C$

Rating

Collector Current — Continuous



Unit

Vdc

Vdc

Vdc

mAdc

mW

mW/°C

mW

mW/°C

°C

MPQ6700

MPQ6501, MPQ6502 For Specifications, See MPQ6001 Data

> MPQ6600A1 For Specifications.

See MPQ6100A Data

Voltage and current are negative for PNP transistors

Motorola Preferred Device



CASE 646-06, STYLE 1 TO-116 TYPE B

THERMAL CHARACTERISTICS

Operating and Storage Junction

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die	151	250	°C/W
	Effective, 4 Die	52	139	°C/W
Coupling Factors	Q1–Q4 or Q2–Q3	34	70	%
	Q1–Q2 or Q3–Q4	2.0	26	%

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS		•		
Collector-Emitter Breakdown Voltage ⁽²⁾ ($I_C = 10 \text{ mAdc}, I_B = 0$)	V(BR)CEO	40	_	Vdc
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu Adc, I_E = 0)$	V(BR)CBO	40	_	Vdc
Emitter-Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$	V(BR)EBO	5.0	_	Vdc
Collector Cutoff Current ($V_{CB} = 30 Vdc, I_E = 0$)	ICBO	_	50	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}, I_{C} = 0$)	IEBO	_	50	nAdc

1. Second Breakdown occurs at power levels greater than 3 times the power dissipation rating.

2. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.



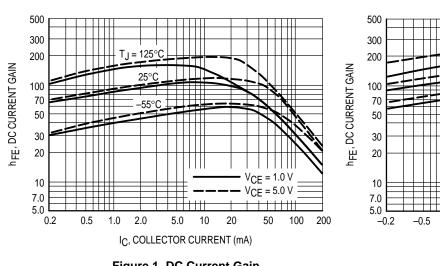
MPQ6700

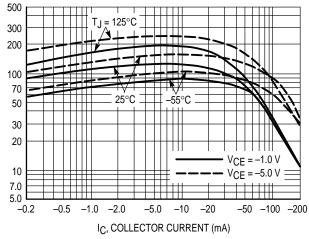
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS(2)				•	
DC Current Gain $(I_{C} = 0.1 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 1.0 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$ $(I_{C} = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$		hFE	30 50 70		_
Collector-Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$		VCE(sat)	_	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$)		V _{BE(sat)}	_	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ⁽²⁾ (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)		fT	200	_	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f =1.0 MHz)		C _{obo}	_	4.5	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	PNP NPN	C _{ibo}		10 8.0	pF

2. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2.0%.

NPN

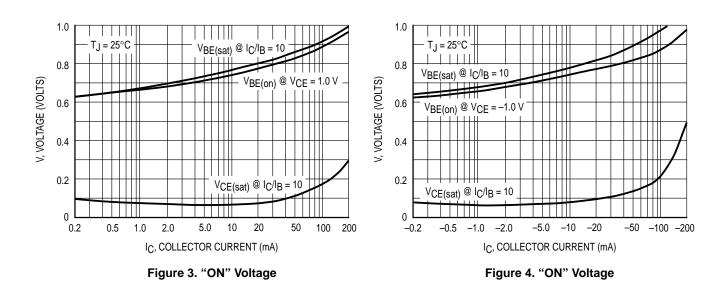




PNP

Figure 1. DC Current Gain





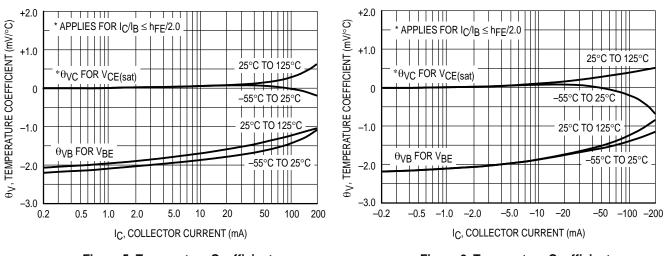
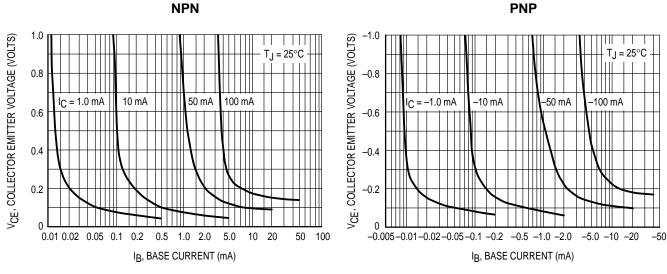
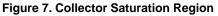


Figure 5. Temperature Coefficients

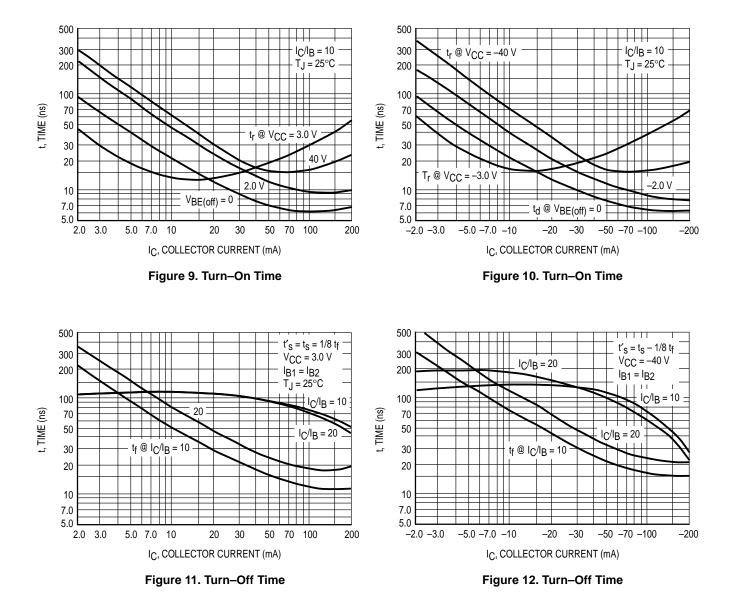
Figure 6. Temperature Coefficients

MPQ6700









Motorola Small-Signal Transistors, FETs and Diodes Device Data

TJ = 25°C

-40



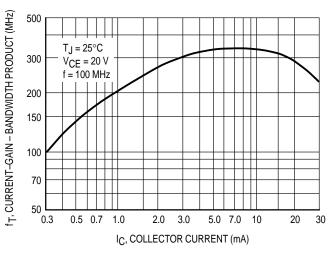


Figure 13. Current–Gain — Bandwidth Product

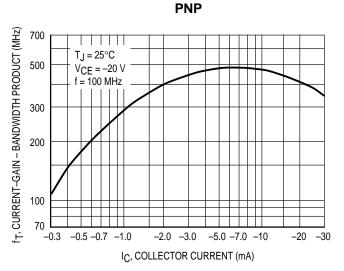


Figure 14. Current–Gain — Bandwidth Product

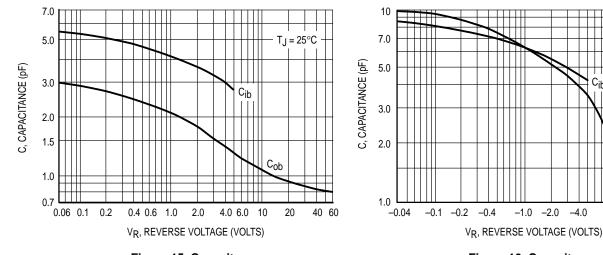


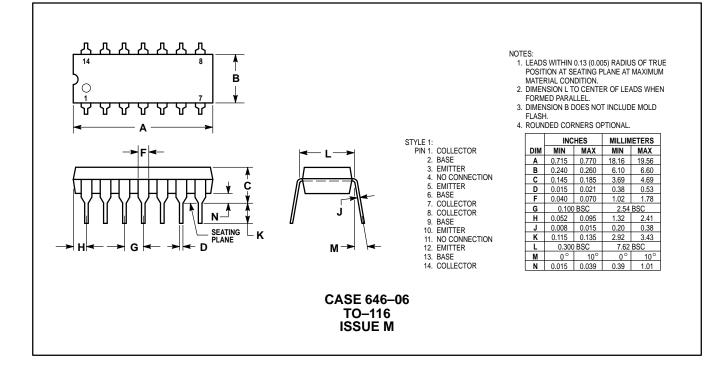
Figure 15. Capacitance

Cib Cob -4.0 -10 -20

Figure 16. Capacitance

MPQ6700

PACKAGE DIMENSIONS



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